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Understanding **Embedded - FPGAs (Field Programmable Gate Array)**

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	157
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p250-fgg256t

I/Os Per Package

ProASIC3 Devices	A3P060	A3P125	A3P250		A3P1000	
Package	I/O Type					
	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O ²	Differential I/O Pairs	Single-Ended I/O ²	Differential I/O Pairs
VQ100	71	71	68	13	–	–
FG144	96	97	97	24	97	25
FG256	–	–	157	38	177	44
FG484	–	–	–	–	300	74
QNG132	–	84	87	19	–	–

Notes:

1. When considering migrating your design to a lower- or higher-density device, refer to the [ProASIC3 FPGA Fabric User's Guide](#) to ensure complying with design and board migration requirements.
2. Each used differential I/O pair reduces the number of available single-ended I/Os by two.
3. FG256 and FG484 are footprint-compatible packages.

Automotive ProASIC3 Device Status

Automotive ProASIC3 Devices	Status
A3P060	Production
A3P125	Production
A3P250	Production
A3P1000	Production

Temperature Grade Offerings

Package	A3P060	A3P125	A3P250	A3P1000
VQ100	C, I, T	C, I, T	C, I, T	–
FG144	C, I, T	C, I, T	C, I, T	C, I, T
FG256	–	–	C, I, T	C, I, T
FG484	–	–	–	C, I, T
QNG132	–	C, I, T	C, I, T	–

Notes:

1. C = Commercial temperature range: 0°C to 70°C
2. I = Industrial temperature range: –40°C to 85°C
3. T = Automotive temperature range: Grade 2 and Grade 1 AEC-Q100
Grade 2 = 105°C T_A and 115°C T_J
Grade 1 = 125°C T_A and 135°C T_J
4. Specifications for Commercial and Industrial grade devices can be found in the [ProASIC3 Flash Family FPGAs datasheet](#).

Speed Grade and Temperature Grade Matrix

Temperature Grade	Std.	–1
T (Grade 1 and Grade 2), Commercial, Industrial	3	3

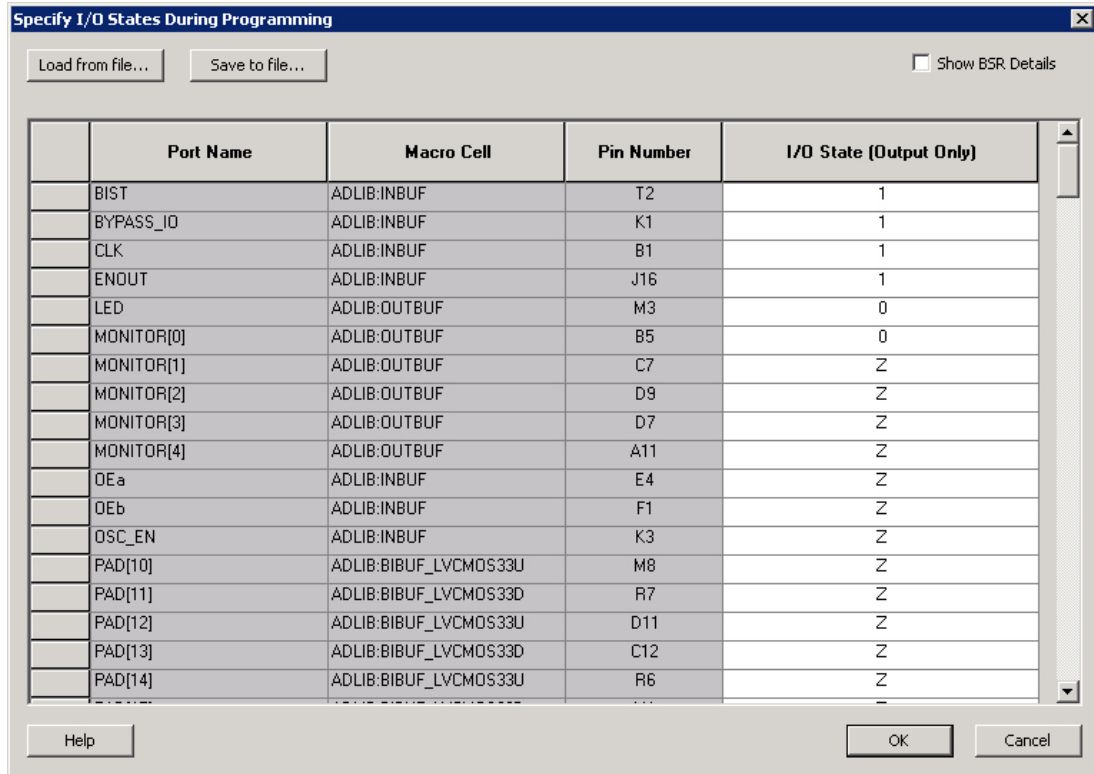
Notes:

1. T = Automotive temperature range: Grade 2 and Grade 1 AEC-Q100
Grade 2 = 105°C T_A and 115°C T_J
Grade 1 = 125°C T_A and 135°C T_J
2. Specifications for Commercial and Industrial grade devices can be found in the [ProASIC3 Flash Family FPGAs datasheet](#).

Contact your local Microsemi SoC Products Group representative for device availability:

<http://www.microsemi.com/soc/contact/default.aspx>.

5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:
 - 1 – I/O is set to drive out logic High
 - 0 – I/O is set to drive out logic Low
 - Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming
 - Z -Tristate: I/O is tristated



The window titled "Specify I/O States During Programming" contains a table with the following data:

	Port Name	Macro Cell	Pin Number	I/O State (Output Only)
	BIST	ADLIB:INBUF	T2	1
	BYPASS_I0	ADLIB:INBUF	K1	1
	CLK	ADLIB:INBUF	B1	1
	ENOUT	ADLIB:INBUF	J16	1
	LED	ADLIB:OUTBUF	M3	0
	MONITOR[0]	ADLIB:OUTBUF	B5	0
	MONITOR[1]	ADLIB:OUTBUF	C7	Z
	MONITOR[2]	ADLIB:OUTBUF	D9	Z
	MONITOR[3]	ADLIB:OUTBUF	D7	Z
	MONITOR[4]	ADLIB:OUTBUF	A11	Z
	OEa	ADLIB:INBUF	E4	Z
	OEb	ADLIB:INBUF	F1	Z
	OSC_EN	ADLIB:INBUF	K3	Z
	PAD[10]	ADLIB:BIBUF_LVCMOS33U	M8	Z
	PAD[11]	ADLIB:BIBUF_LVCMOS33D	R7	Z
	PAD[12]	ADLIB:BIBUF_LVCMOS33U	D11	Z
	PAD[13]	ADLIB:BIBUF_LVCMOS33D	C12	Z
	PAD[14]	ADLIB:BIBUF_LVCMOS33U	R6	Z

The window also includes buttons for "Load from file...", "Save to file...", "Show BSR Details" (checkbox), "Help", "OK", and "Cancel".

Figure 1-4 • I/O States During Programming Window

6. Click **OK** to return to the FlashPoint – Programming File Generator window.

Note: I/O States During programming are saved to the ADB and resulting programming files after completing programming file generation.

2 – Automotive ProASIC3 DC and Switching Characteristics

General Specifications

Operating Conditions

Stresses beyond those listed in [Table 2-1](#) may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximums are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in [Table 2-2](#) on [page 2-2](#) is not implied.

Table 2-1 • Absolute Maximum Ratings

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	V
VCCI	DC I/O output buffer supply voltage	–0.3 to 3.75	V
VMV	DC I/O input buffer supply voltage	–0.3 to 3.75	V
VI	I/O input voltage	–0.3 V to 3.6 V (when I/O hot insertion mode is enabled) –0.3 V to (V _{CCI} + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot-insertion mode is disabled)	V
T _{STG} ²	Storage temperature	–65 to +150	°C
T _J ²	Junction temperature	+150	°C

Notes:

1. The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in [Table 2-3](#) on [page 2-3](#).
2. For flash programming and retention maximum limits, refer to [Figure 2-1](#) on [page 2-2](#). For recommended operating limits, refer to [Table 2-2](#) on [page 2-2](#).

Table 2-37 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	STD	0.64	8.06	0.05	1.12	0.46	8.20	7.03	1.26	1.27	8.20	7.027	ns
	-1	0.55	6.85	0.04	.095	0.39	6.98	5.98	1.26	1.27	6.98	5.978	ns
6 mA	STD	0.64	5.03	0.05	1.12	0.46	5.13	4.27	1.42	1.56	5.13	4.267	ns
	-1	0.55	4.28	0.04	0.95	0.39	4.36	3.63	1.42	1.56	4.36	3.63	ns
8 mA	STD	0.64	5.03	0.05	1.12	0.46	5.13	4.27	1.42	1.56	5.13	4.267	ns
	-1	0.55	4.28	0.04	0.95	0.39	4.36	3.63	1.42	1.56	4.36	3.63	ns
12 mA	STD	0.64	3.53	0.05	1.12	0.46	1.74	1.43	3.12	3.60	1.74	1.427	ns
	-1	0.55	3.01	0.04	0.95	0.39	1.74	1.43	2.65	3.06	1.74	1.428	ns
16 mA	STD	0.64	3.53	0.05	1.12	0.46	1.74	1.43	3.12	3.60	1.74	1.427	ns
	-1	0.55	3.01	0.04	0.95	0.39	1.74	1.43	2.65	3.06	1.74	1.428	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-38 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	STD	0.64	10.82	0.05	1.12	0.46	11.02	9.42	1.26	1.20	11.02	9.419	ns
	-1	0.55	9.21	0.04	0.95	0.39	9.38	8.01	1.26	1.20	9.38	8.012	ns
6 mA	STD	0.64	7.49	0.05	1.12	0.46	7.63	6.58	1.43	1.48	7.63	6.58	ns
	-1	0.55	6.37	0.04	0.95	0.39	6.49	5.60	1.43	1.49	6.49	5.598	ns
8 mA	STD	0.64	7.49	0.05	1.12	0.46	7.63	6.58	1.43	1.48	7.63	6.58	ns
	-1	0.55	6.37	0.04	0.95	0.39	6.49	5.60	1.43	1.49	6.49	5.598	ns
12 mA	STD	0.64	5.64	0.05	1.12	0.46	5.75	5.04	1.54	1.67	5.75	5.042	ns
	-1	0.55	4.80	0.04	0.95	0.39	4.89	4.29	1.54	1.67	4.89	4.289	ns
16 mA	STD	0.64	5.64	0.05	1.12	0.46	5.75	5.04	1.54	1.67	5.75	5.042	ns
	-1	0.55	4.80	0.04	0.95	0.39	4.89	4.29	1.54	1.67	4.89	4.289	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-64 • 1.8 V LVCMOS Low Slew

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	16.80	0.05	1.40	0.45	14.60	16.01	1.20	0.77	17.02	18.43	ns
	-1	0.53	14.29	0.04	1.19	0.38	12.42	13.62	1.20	0.77	14.48	15.68	ns
4 mA	STD	0.63	11.33	0.05	1.40	0.45	10.53	10.71	1.42	1.31	12.95	13.13	ns
	-1	0.53	9.64	0.04	1.19	0.38	8.96	9.11	1.42	1.31	11.01	11.17	ns
6 mA	STD	0.63	8.71	0.05	1.40	0.45	8.19	7.92	1.57	1.57	10.61	10.34	ns
	-1	0.53	7.41	0.04	1.19	0.38	6.97	6.74	1.57	1.57	9.03	8.79	ns
8 mA	STD	0.63	8.12	0.05	1.40	0.45	8.19	7.92	1.57	1.57	10.61	10.34	ns
	-1	0.53	6.90	0.04	1.19	0.38	6.97	6.74	1.57	1.57	9.03	8.79	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-65 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	I_{OL}	I_{OH}	I_{OSL}	I_{OSH}	I_{IL}	I_{IH}
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA^2	μA^2
2 mA	-0.3	0.30 * V_{CCI}	0.7 * V_{CCI}	3.6	0.25 * V_{CCI}	0.75 * V_{CCI}	2	2	16	13	10	10
4 mA	-0.3	0.30 * V_{CCI}	0.7 * V_{CCI}	3.6	0.25 * V_{CCI}	0.75 * V_{CCI}	4	4	33	25	10	10
6 mA	-0.3	0.30 * V_{CCI}	0.7 * V_{CCI}	3.6	0.25 * V_{CCI}	0.75 * V_{CCI}	6	6	39	32	10	10
8 mA	-0.3	0.30 * V_{CCI}	0.7 * V_{CCI}	3.6	0.25 * V_{CCI}	0.75 * V_{CCI}	8	8	55	66	10	10
12 mA	-0.3	0.30 * V_{CCI}	0.7 * V_{CCI}	3.6	0.25 * V_{CCI}	0.75 * V_{CCI}	12	12	55	66	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 125°C junction temperature.
3. Software default selection highlighted in gray.

Timing Characteristics

Table 2-68 • 1.5 V LVC MOS High Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	9.35	0.05	1.61	0.46	7.63	9.35	1.87	1.50	10.13	11.851	ns
	-1	0.55	7.95	0.04	1.37	0.39	6.49	7.95	1.87	1.50	8.62	10.081	ns
4 mA	STD	0.64	5.94	0.05	1.61	0.46	5.42	5.94	2.07	1.84	7.92	8.442	ns
	-1	0.55	5.05	0.04	1.37	0.39	4.61	5.05	2.07	1.85	6.74	7.181	ns
6 mA	STD	0.64	5.22	0.05	1.61	0.46	5.09	5.22	2.11	1.93	7.59	7.718	ns
	-1	0.55	4.44	0.04	1.37	0.39	4.33	4.44	2.11	1.93	6.45	6.566	ns
8 mA	STD	0.64	4.56	0.05	1.61	0.46	2.25	1.98	4.41	4.70	3.46	3.211	ns
	-1	0.55	3.88	0.04	1.37	0.39	2.25	1.98	3.75	4.00	3.46	3.213	ns
12 mA	STD	0.64	4.56	0.05	1.61	0.46	2.25	1.98	4.41	4.70	3.46	3.211	ns
	-1	0.55	3.88	0.04	1.37	0.39	2.25	1.98	3.75	4.00	3.46	3.213	ns

Notes:

- Software default selection highlighted in gray.
- For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-69 • 1.5 V LVC MOS Low Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	14.29	0.05	1.45	0.46	14.32	14.29	1.88	1.43	16.82	16.794	ns
	-1	0.55	12.16	0.04	1.23	0.39	12.18	12.16	1.88	1.43	14.31	14.286	ns
4 mA	STD	0.64	11.19	0.05	1.45	0.46	11.40	10.67	2.07	1.77	13.90	13.175	ns
	-1	0.55	9.52	0.04	1.23	0.39	9.70	9.08	2.07	1.77	11.82	11.207	ns
6 mA	STD	0.64	10.44	0.05	1.45	0.46	10.63	9.94	2.12	1.86	13.13	12.442	ns
	-1	0.55	8.88	0.04	1.23	0.39	9.04	8.46	2.12	1.86	11.17	10.584	ns
8 mA	STD	0.64	9.96	0.05	1.45	0.46	10.15	9.94	2.18	2.19	12.65	12.445	ns
	-1	0.55	8.47	0.04	1.23	0.39	8.63	8.46	2.19	2.20	10.76	10.586	ns
12 mA	STD	0.64	9.96	0.05	1.45	0.46	10.15	9.94	2.18	2.19	12.65	12.445	ns
	-1	0.55	8.47	0.04	1.23	0.39	8.63	8.46	2.19	2.20	10.76	10.586	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-90 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{iCLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{iSUD}	Data Setup Time for the Input Data Register	C, A
t_{iHD}	Data Hold Time for the Input Data Register	C, A
t_{iSUE}	Enable Setup Time for the Input Data Register	B, A
t_{iHE}	Enable Hold Time for the Input Data Register	B, A
t_{iPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{iREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{iRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-15 on page 2-53 for more information.

Output Register

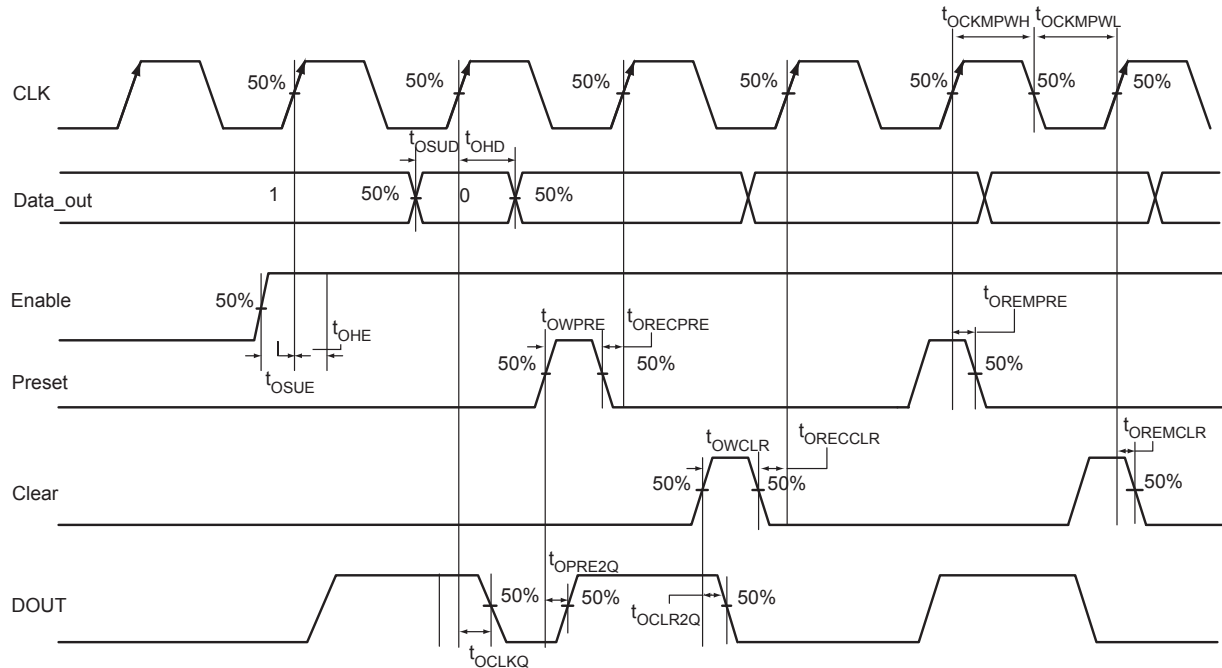


Figure 2-18 • Output Register Timing Diagram

Timing Characteristics

Table 2-94 • Output Data Register Propagation Delays
Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-1	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.72	0.84	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.38	0.45	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	0.00	ns
t_{OSUE}	Enable Setup Time for the Output Data Register	0.53	0.63	ns
t_{OHE}	Enable Hold Time for the Output Data Register	0.00	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.98	1.15	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.98	1.15	ns
t_{OEMCLR}	Asynchronous Clear Removal Time for the Output Data Register	0.00	0.00	ns
t_{OECCLR}	Asynchronous Clear Recovery Time for the Output Data Register	0.27	0.32	ns
t_{OEMPRE}	Asynchronous Preset Removal Time for the Output Data Register	0.00	0.00	ns
t_{OECPRE}	Asynchronous Preset Recovery Time for the Output Data Register	0.27	0.32	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.25	0.30	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.25	0.30	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.41	0.48	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-97 • Output Enable Register Propagation Delays
Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.53	0.62	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.37	0.44	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.52	0.61	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.79	0.93	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.79	0.93	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.27	0.31	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.27	0.31	ns
$t_{OEWCCLR}$	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.25	0.30	ns
t_{OEWPPE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-103 • Output DDR Propagation Delays
Commercial-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1	Std.	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	0.84	0.98	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	0.45	0.53	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	0.45	0.53	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	0.96	1.12	ns
$t_{\text{DDROREMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	0.00	ns
$t_{\text{DDRORECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.27	0.31	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.25	0.30	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width High for the Output DDR	0.41	0.48	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width Low for the Output DDR	0.37	0.43	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	309	263	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Global Resource Characteristics

A3P250 Clock Tree Topology

Clock delays are device-specific. Figure 2-28 is an example of a global tree used for clock routing. The global tree presented in Figure 2-28 is driven by a CCC located on the west side of the A3P250 device. It is used to drive all D-flip-flops in the device.

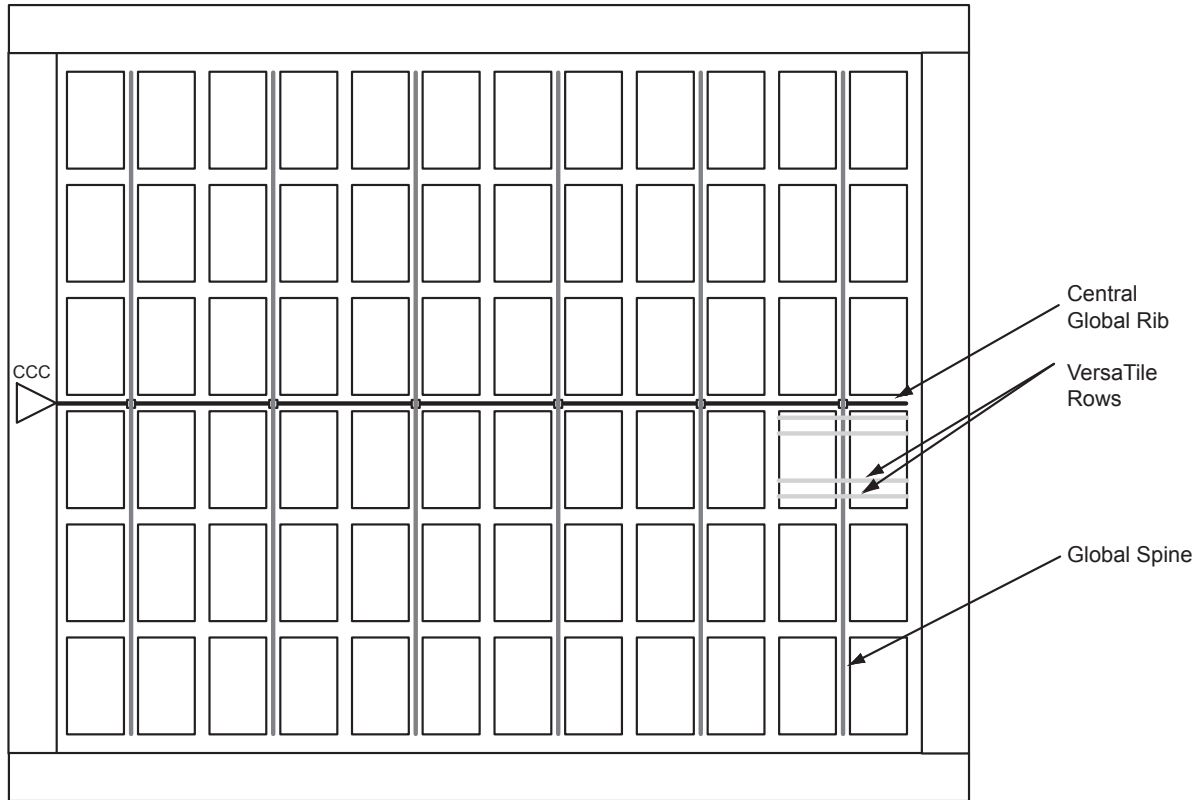


Figure 2-28 • Example of Global Tree Use in an A3P250 Device for Clock Routing

Table 2-110 • A3P125 Global Resource
Commercial-Case Conditions: $T_J = 135^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.93	1.22	1.09	1.43	ns
t_{RCKH}	Input High Delay for Global Clock	0.92	1.26	1.08	1.49	ns
t_{RCKMPWH}	Minimum Pulse Width High for Global Clock	0.80		0.94		ns
t_{RCKMPWL}	Minimum Pulse Width Low for Global Clock	0.98		1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.35		0.41	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-111 • A3P125 Global Resource
Commercial-Case Conditions: $T_J = 115^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.90	1.19	1.06	1.40	ns
t_{RCKH}	Input High Delay for Global Clock	0.90	1.23	1.05	1.45	ns
t_{RCKMPWH}	Minimum Pulse Width High for Global Clock	0.80		0.94		ns
t_{RCKMPWL}	Minimum Pulse Width Low for Global Clock	0.98		1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.34		0.40	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Clock Conditioning Circuits

CCC Electrical Specifications

Timing Characteristics

Table 2-116 • Automotive ProASIC3 CCC/PLL Specification

Parameter	Minimum	Typical	Maximum	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		350	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		350	MHz
Delay Increments in Programmable Delay Blocks ^{1, 2}		160 ³		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Input Period Jitter			1.5	ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT}	Max Peak-to-Peak Period Jitter			
	1 Global Network Used		3 Global Networks Used	
0.75 MHz to 24 MHz	0.50%		0.70%	
24 MHz to 100 MHz	1.00%		1.20%	
100 MHz to 250 MHz	1.75%		2.00%	
250 MHz to 350 MHz	2.50%		5.60%	
Acquisition Time				
(A3P250 and A3P1000 only) LockControl = 0			300	μs
LockControl = 1			300	μs
(all other dies) LockControl = 0			300	μs
LockControl = 1			6.0	ms
Tracking Jitter ⁴				
(A3P250 and A3P1000 only) LockControl = 0			1.6	ns
LockControl = 1			1.6	ns
(all other dies) LockControl = 0			1.6	ns
LockControl = 1			0.8	ns
Output Duty Cycle	48.5		51.5	%
Delay Range in Block: Programmable Delay 1 ^{1, 2}	0.6		5.56	ns
Delay Range in Block: Programmable Delay 2 ^{1, 2}	0.025		5.56	ns
Delay Range in Block: Fixed Delay ^{1, 2}		2.2		ns

Notes:

1. This delay is a function of voltage and temperature. See [Table 2-5 on page 2-5](#) for deratings.
2. $T_J = 25^\circ\text{C}$, $V_{CC} = 1.5\text{ V}$
3. When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help associated with the core for more information.
4. Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.

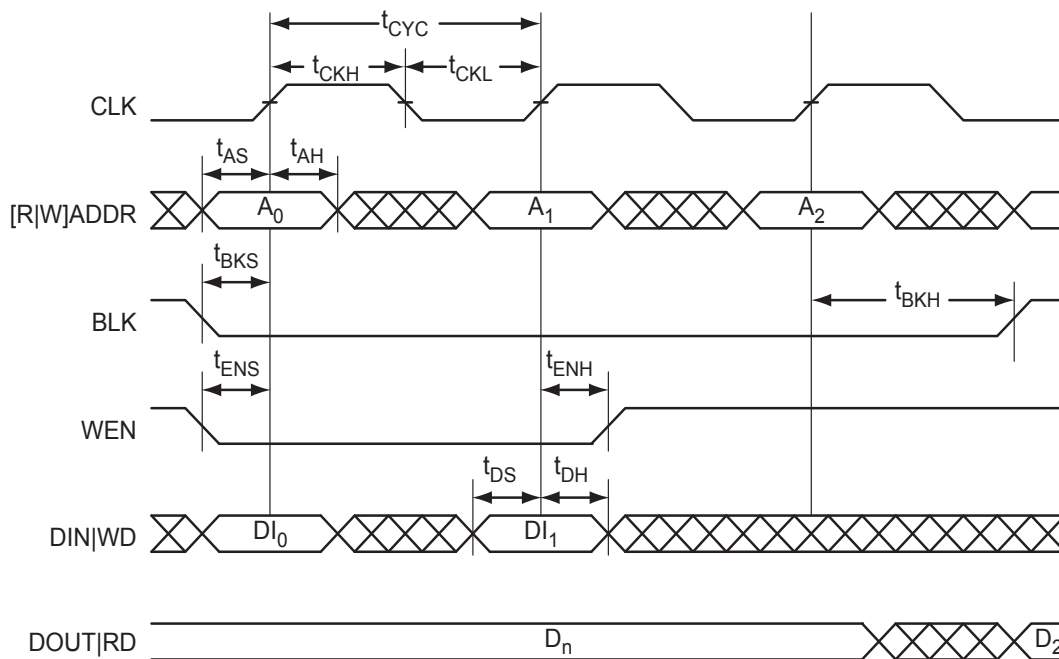


Figure 2-33 • RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.

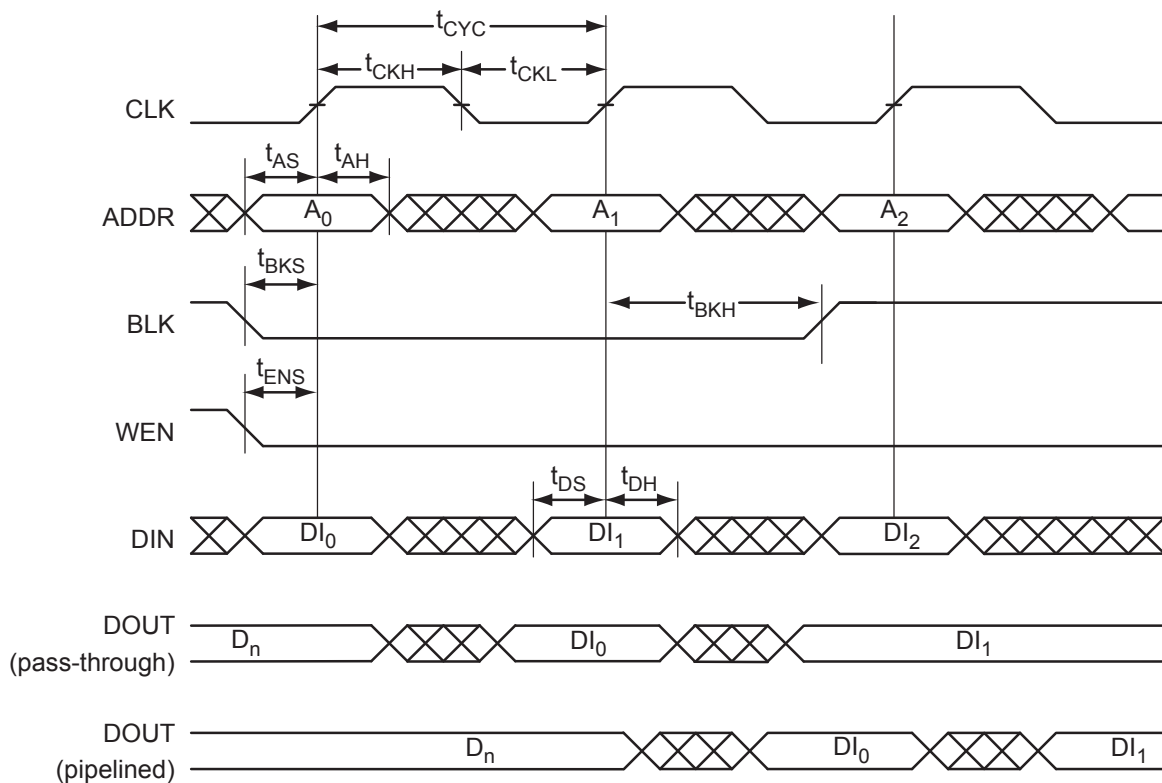


Figure 2-34 • RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 Only.

VQ100	
Pin Number	A3P060 Function
1	GND
2	GAA2/IO51RSB1
3	IO52RSB1
4	GAB2/IO53RSB1
5	IO95RSB1
6	GAC2/IO94RSB1
7	IO93RSB1
8	IO92RSB1
9	GND
10	GFB1/IO87RSB1
11	GFB0/IO86RSB1
12	VCOMPLF
13	GFA0/IO85RSB1
14	VCCPLF
15	GFA1/IO84RSB1
16	GFA2/IO83RSB1
17	VCC
18	VCCIB1
19	GEC1/IO77RSB1
20	GEB1/IO75RSB1
21	GEB0/IO74RSB1
22	GEA1/IO73RSB1
23	GEA0/IO72RSB1
24	VMV1
25	GNDQ
26	GEA2/IO71RSB1
27	GEB2/IO70RSB1
28	GEC2/IO69RSB1
29	IO68RSB1
30	IO67RSB1
31	IO66RSB1
32	IO65RSB1
33	IO64RSB1
34	IO63RSB1

VQ100	
Pin Number	A3P060 Function
35	IO62RSB1
36	IO61RSB1
37	VCC
38	GND
39	VCCIB1
40	IO60RSB1
41	IO59RSB1
42	IO58RSB1
43	IO57RSB1
44	GDC2/IO56RSB1
45	GDB2/IO55RSB1
46	GDA2/IO54RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO49RSB0
58	GDC0/IO46RSB0
59	GDC1/IO45RSB0
60	GCC2/IO43RSB0
61	GCB2/IO42RSB0
62	GCA0/IO40RSB0
63	GCA1/IO39RSB0
64	GCC0/IO36RSB0
65	GCC1/IO35RSB0
66	VCCIB0
67	GND
68	VCC

VQ100	
Pin Number	A3P060 Function
69	IO31RSB0
70	GBC2/IO29RSB0
71	GBB2/IO27RSB0
72	IO26RSB0
73	GBA2/IO25RSB0
74	VMV0
75	GNDQ
76	GBA1/IO24RSB0
77	GBA0/IO23RSB0
78	GBB1/IO22RSB0
79	GBB0/IO21RSB0
80	GBC1/IO20RSB0
81	GBC0/IO19RSB0
82	IO18RSB0
83	IO17RSB0
84	IO15RSB0
85	IO13RSB0
86	IO11RSB0
87	VCCIB0
88	GND
89	VCC
90	IO10RSB0
91	IO09RSB0
92	IO08RSB0
93	GAC1/IO07RSB0
94	GAC0/IO06RSB0
95	GAB1/IO05RSB0
96	GAB0/IO04RSB0
97	GAA1/IO03RSB0
98	GAA0/IO02RSB0
99	IO01RSB0
100	IO00RSB0

VQ100	
Pin Number	A3P125 Function
1	GND
2	GAA2/IO67RSB1
3	IO68RSB1
4	GAB2/IO69RSB1
5	IO132RSB1
6	GAC2/IO131RSB1
7	IO130RSB1
8	IO129RSB1
9	GND
10	GFB1/IO124RSB1
11	GFB0/IO123RSB1
12	VCOMPLF
13	GFA0/IO122RSB1
14	VCCPLF
15	GFA1/IO121RSB1
16	GFA2/IO120RSB1
17	VCC
18	VCCIB1
19	GEC0/IO111RSB1
20	GEB1/IO110RSB1
21	GEB0/IO109RSB1
22	GEA1/IO108RSB1
23	GEA0/IO107RSB1
24	VMV1
25	GNDQ
26	GEA2/IO106RSB1
27	GEB2/IO105RSB1
28	GEC2/IO104RSB1
29	IO102RSB1
30	IO100RSB1
31	IO99RSB1
32	IO97RSB1
33	IO96RSB1
34	IO95RSB1
35	IO94RSB1
36	IO93RSB1

VQ100	
Pin Number	A3P125 Function
37	VCC
38	GND
39	VCCIB1
40	IO87RSB1
41	IO84RSB1
42	IO81RSB1
43	IO75RSB1
44	GDC2/IO72RSB1
45	GDB2/IO71RSB1
46	GDA2/IO70RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO65RSB0
58	GDC0/IO62RSB0
59	GDC1/IO61RSB0
60	GCC2/IO59RSB0
61	GCB2/IO58RSB0
62	GCA0/IO56RSB0
63	GCA1/IO55RSB0
64	GCC0/IO52RSB0
65	GCC1/IO51RSB0
66	VCCIB0
67	GND
68	VCC
69	IO47RSB0
70	GBC2/IO45RSB0
71	GBB2/IO43RSB0
72	IO42RSB0

VQ100	
Pin Number	A3P125 Function
73	GBA2/IO41RSB0
74	VMV0
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO32RSB0
83	IO28RSB0
84	IO25RSB0
85	IO22RSB0
86	IO19RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	IO09RSB0
94	IO07RSB0
95	GAC1/IO05RSB0
96	GAC0/IO04RSB0
97	GAB1/IO03RSB0
98	GAB0/IO02RSB0
99	GAA1/IO01RSB0
100	GAA0/IO00RSB0

FG256	
Pin Number	A3P1000 Function
P9	IO137RSB2
P10	IO134RSB2
P11	IO128RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO113NDB1
R1	GEA1/IO188PDB3
R2	GEA0/IO188NDB3
R3	IO184RSB2
R4	GEC2/IO185RSB2
R5	IO168RSB2
R6	IO163RSB2
R7	IO157RSB2
R8	IO149RSB2
R9	IO143RSB2
R10	IO138RSB2
R11	IO131RSB2
R12	IO125RSB2
R13	GDB2/IO115RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO183RSB2
T3	GEB2/IO186RSB2
T4	IO172RSB2
T5	IO170RSB2
T6	IO164RSB2
T7	IO158RSB2
T8	IO153RSB2
T9	IO142RSB2
T10	IO135RSB2
T11	IO130RSB2
T12	GDC2/IO116RSB2

FG256	
Pin Number	A3P1000 Function
T13	IO120RSB2
T14	GDA2/IO114RSB2
T15	TMS
T16	GND

FG484		FG484		FG484	
Pin Number	A3P1000 Function	Pin Number	A3P1000 Function	Pin Number	A3P1000 Function
A1	GND	B15	IO63RSB0	D7	GAB0/IO02RSB0
A2	GND	B16	IO66RSB0	D8	IO16RSB0
A3	VCCIB0	B17	IO68RSB0	D9	IO22RSB0
A4	IO07RSB0	B18	IO70RSB0	D10	IO28RSB0
A5	IO09RSB0	B19	NC	D11	IO35RSB0
A6	IO13RSB0	B20	NC	D12	IO45RSB0
A7	IO18RSB0	B21	VCCIB1	D13	IO50RSB0
A8	IO20RSB0	B22	GND	D14	IO55RSB0
A9	IO26RSB0	C1	VCCIB3	D15	IO61RSB0
A10	IO32RSB0	C2	IO220PDB3	D16	GBB1/IO75RSB0
A11	IO40RSB0	C3	NC	D17	GBA0/IO76RSB0
A12	IO41RSB0	C4	NC	D18	GBA1/IO77RSB0
A13	IO53RSB0	C5	GND	D19	GND
A14	IO59RSB0	C6	IO10RSB0	D20	NC
A15	IO64RSB0	C7	IO14RSB0	D21	NC
A16	IO65RSB0	C8	VCC	D22	NC
A17	IO67RSB0	C9	V _{CC}	E1	IO219NDB3
A18	IO69RSB0	C10	IO30RSB0	E2	NC
A19	NC	C11	IO37RSB0	E3	GND
A20	VCCIB0	C12	IO43RSB0	E4	GAB2/IO224PDB3
A21	GND	C13	NC	E5	GAA2/IO225PDB3
A22	GND	C14	VCC	E6	GNDQ
B1	GND	C15	VCC	E7	GAB1/IO03RSB0
B2	VCCIB3	C16	NC	E8	IO17RSB0
B3	NC	C17	NC	E9	IO21RSB0
B4	IO06RSB0	C18	GND	E10	IO27RSB0
B5	IO08RSB0	C19	NC	E11	IO34RSB0
B6	IO12RSB0	C20	NC	E12	IO44RSB0
B7	IO15RSB0	C21	NC	E13	IO51RSB0
B8	IO19RSB0	C22	VCCIB1	E14	IO57RSB0
B9	IO24RSB0	D1	IO219PDB3	E15	GBC1/IO73RSB0
B10	IO31RSB0	D2	IO220NDB3	E16	GBB0/IO74RSB0
B11	IO39RSB0	D3	NC	E17	IO71RSB0
B12	IO48RSB0	D4	GND	E18	GBA2/IO78PDB1
B13	IO54RSB0	D5	GAA0/IO00RSB0	E19	IO81PDB1
B14	IO58RSB0	D6	GAA1/IO01RSB0	E20	GND

Revision	Changes	Page
Revision 2 (continued)	The "Pin Descriptions and Packaging" chapter has been added (SAR 34767),	3-1
	The "VQ100" pin table for A3P125 has been added (SAR 37944).	4-3
	Package names used in the "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 34767).	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "Automotive ProASIC3 Device Status" table on page II indicates the status for each device in the device family.	N/A

Revision	Changes	Page
Revision 1 (Dec 2009) Product Brief v1.1 Packaging v1.1	The QNG132 package was added to the "Automotive ProASIC3 Product Family" table, "I/Os Per Package" table, "Automotive ProASIC3 Ordering Information", and "Temperature Grade Offerings".	I – IV
	Pin tables for A3P125 and A3P250 were added for the "QN132" package.	4-6